

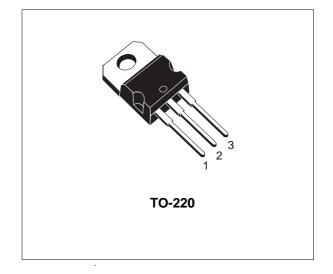
BUL138

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- LOW SPREAD OF DYNAMIC PARAMETERS
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C

APPLICATIONS

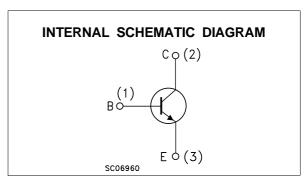
- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- FLYBACK AND FORWARD SINGLE TRANSISTOR LOW POWER CONVERTERS



DESCRIPTION

The BUL138 is manufactured using high voltage Multi Epitaxial Planar technology for high switching speeds and high voltage capability. It uses a Cellular Emitter structure with planar edge termination to enhance switching speeds.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vces	Collector-Emitter Voltage (V _{BE} = 0)	800	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	400	V
V_{EBO}	Emitter-Base Voltage (I _C = 0)	9	V
Ic	Collector Current	5	А
I _{CM}	Collector Peak Current (t _p < 5 ms)	10	А
I _B	Base Current	2	А
I _{BM}	Base Peak Current (t _p < 5 ms)	4	А
P _{tot}	Total Dissipation at T _c = 25 °C	80	W
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

June 2001 1/6

THERMAL DATA

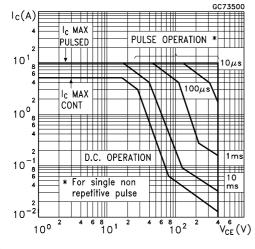
R _{thj-case}	Thermal Resistance Junction-case	Max	1.56	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max	62.5	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

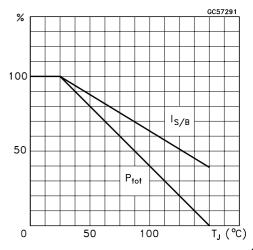
Symbol	nbol Parameter Test Conditions		Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 800 V V _{CE} = 800 V T _j = 125 °C			100 500	μΑ μΑ
I _{CEO}	Collector Cut-off Current (I _B = 0)	V _{CE} = 400 V			250	μΑ
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	I _C = 100 mA L = 25 mH	400			V
V_{EBO}	Emitter-Base Voltage	I _E = 10 mA	9			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$\begin{array}{cccccccccccccccccccccccccccccccccccc$		0.7	0.5 0.7 1 1	> > > > > > > > > > > > > > > > > > >
V _{BE(sat)*}	Base-Emitter Saturation Voltage				1.1 1.3 1.5	V V V
h _{FE} *	DC Current Gain	I _C = 2 A	8 10		40	
ts	RESISTIVE LOAD Storage Time	$I_C = 2 A$ $I_{B1} = -I_{B2} = 0.4 A$ $V_{CC} = 250 V$	2.4		3.5	μs
t _s t _f	INDUCTIVE LOAD Storage Time Fall Time	$\begin{split} I_{C} &= 2 \; A & I_{B1} &= 0.4 \; A \\ V_{BE(off)} &= -5 \; V & R_{BB} &= 0 \; \Omega \\ V_{CL} &= 250 \; V & L &= 200 \; \mu H \end{split}$		0.7 50	1.4 100	μs ns
ts tf	INDUCTIVE LOAD Storage Time Fall Time	$I_{C} = 2 \text{ A}$ $I_{B1} = 0.4 \text{ A}$ $V_{BE(off)} = -5V$ $R_{BB} = 0 \Omega$ $V_{CL} = 250 \text{ V}$ $L = 200 \mu\text{H}$ $T_{i} = 125 ^{\circ}\text{C}$		1 75		μs ns

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Areas

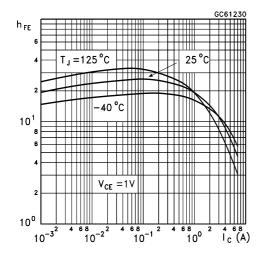


Derating Curve

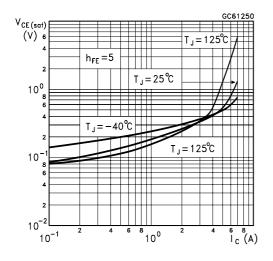


47

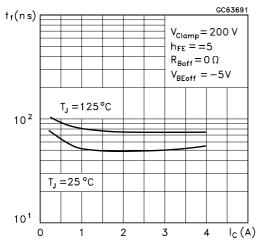
DC Current Gain



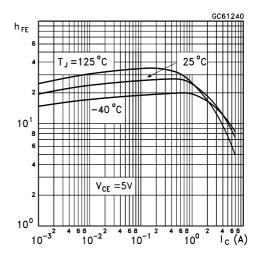
Collector-Emitter Saturation Voltage



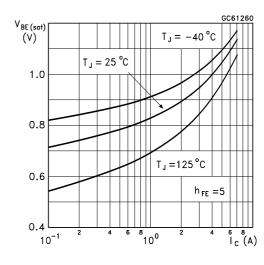
Inductive Fall Time



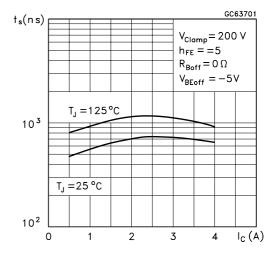
DC Current Gain



Base-Emitter Saturation Voltage

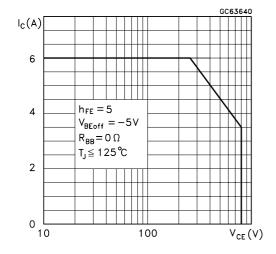


Inductive Storage Time

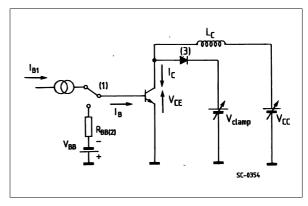


477

Reverse Biased SOA



RBSOA and Inductive Load Switching Test Circuits

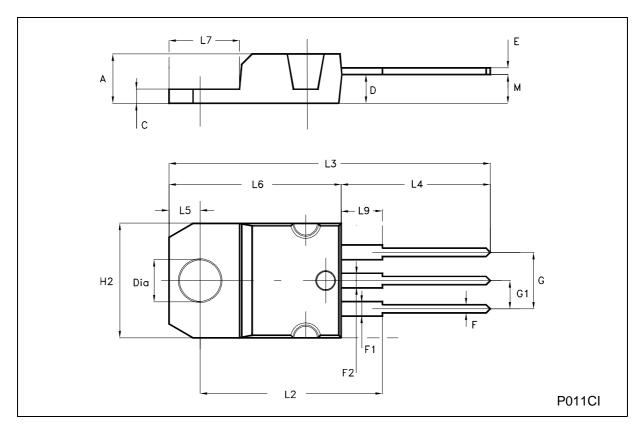


- 1) Fast electronic switch
- 2) Non-inductive Resistor3) Fast recovery rectifier

4/6

TO-220 MECHANICAL DATA

DIM.	mm		inch			
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
С	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
Е	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
М		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2001 STMicroelectronics – Printed in Italy – All Rights Reserved STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

http://www.st.com

47/

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by STMicroelectronics manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460

2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMMTA92QTA

2N2369ADCSM 2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E

MCH4021-TL-E US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR

EMT2T2R MCH6102-TL-E FP204-TL-E NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH
TL-E NSV40301MZ4T1G NTE101